

## Supporting Information

# Interfacial engineering at the 2D/3D heterojunction for high-performance perovskite solar cells

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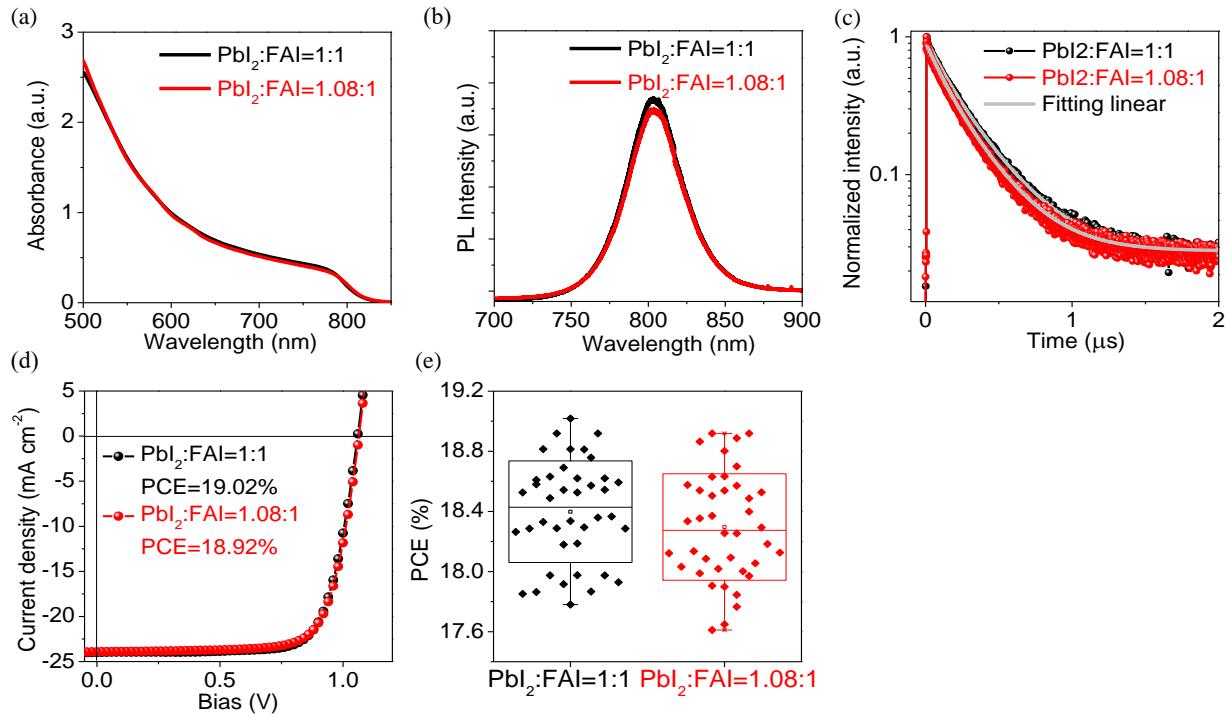
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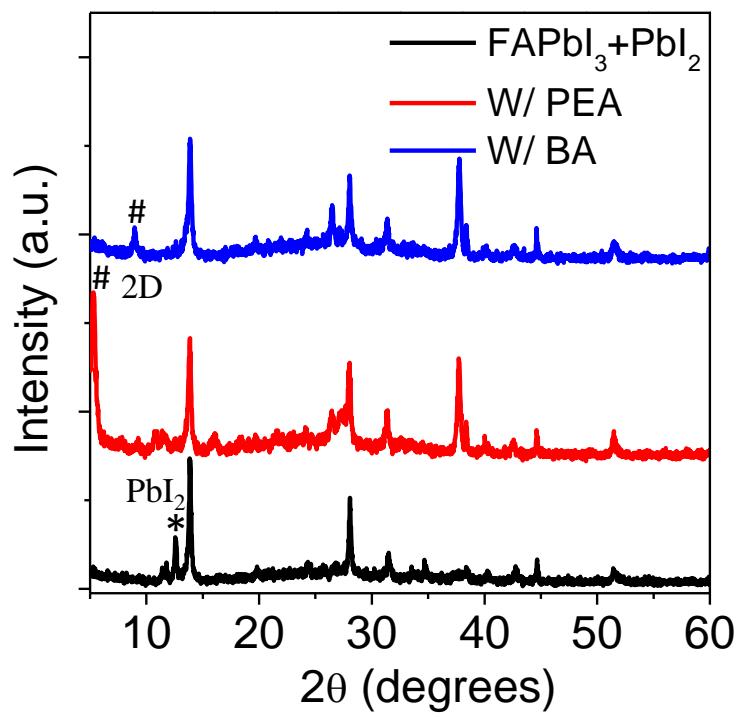
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KEYWORDS: 2D/3D heterojunction, perovskite solar cell, ligand chemistry, interfacial mechanism, high-performance

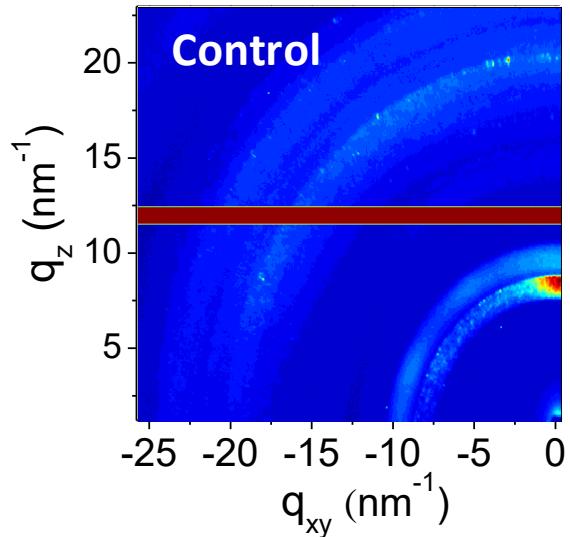
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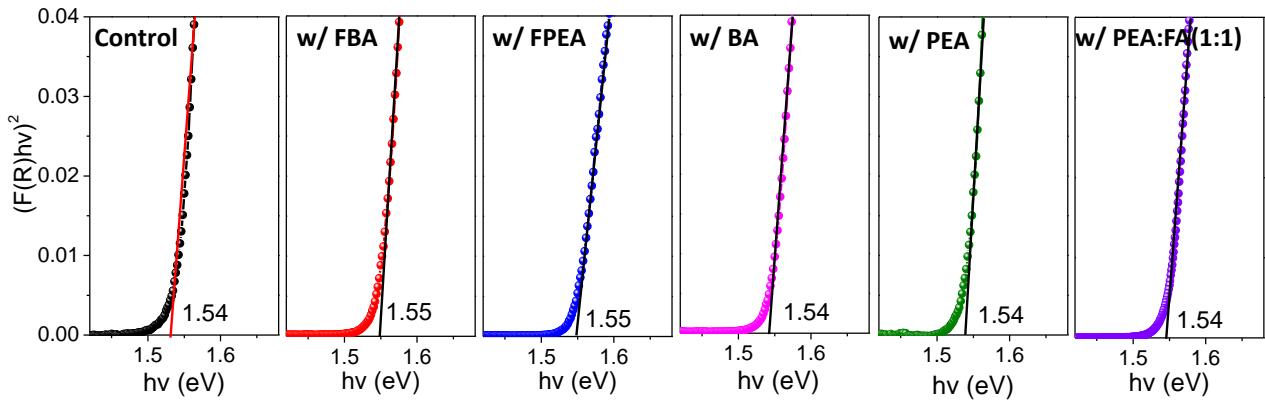
**Figure S1.** (a-c) Steady-state photoluminescence (PL), time-resolved PL spectroscopy (TRPL) and absorption spectra of the FAPbI<sub>3</sub> films with different molar ratio of PbI<sub>2</sub> and FAI. (d) J-V curves of champion devices. (e) Statistics of 40 devices for FAPbI<sub>3</sub> films with different molar ratio of PbI<sub>2</sub> and FAI. Negligible variations in the absorption, emission, carrier lifetime and device performance were observed despite of an extra PbI<sub>2</sub> was introduced, which suggests that the impact of PbI<sub>2</sub> passivation can be excluded.



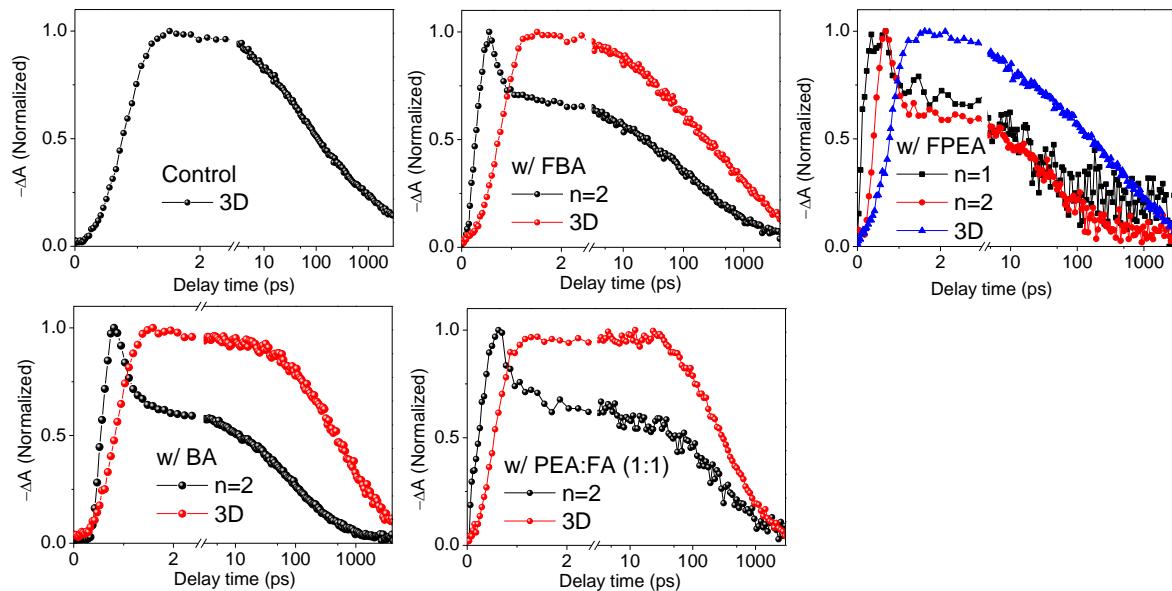
**Figure S2.** X-ray diffraction (XRD) patterns of the FAPbI<sub>3</sub>+PbI<sub>2</sub> and 2D/3D films. Peaks denoted with star and pound signs originate from PbI<sub>2</sub> and 2D perovskite phases.



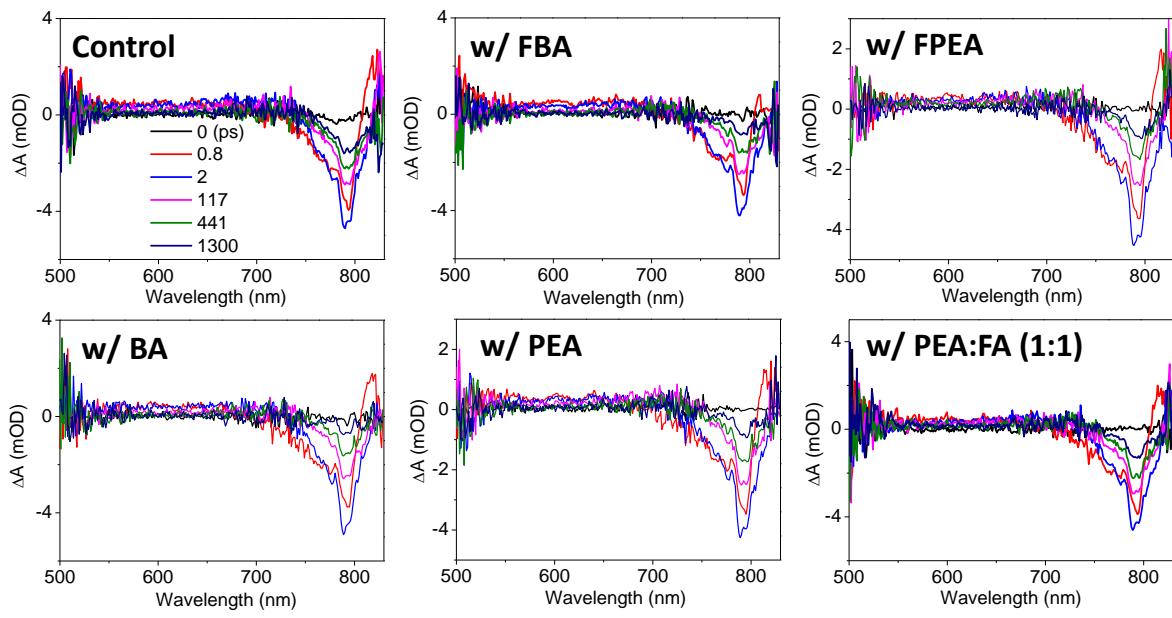
**Figure S3.** *Ex situ* GIWAXS pattern of the control film.



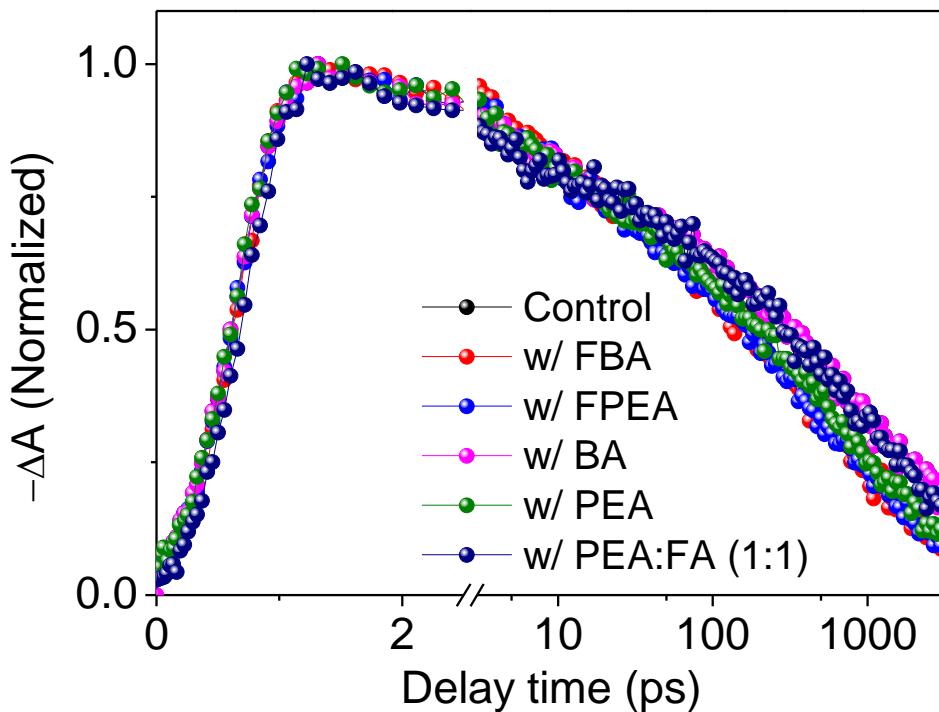
**Figure S4.** Tauc plots for the control, FBA-, FPEA-, BA-, PEA- and PEA:FA(1:1)-based 2D/3D perovskites determining the similar bandgap ( $E_g$ ).



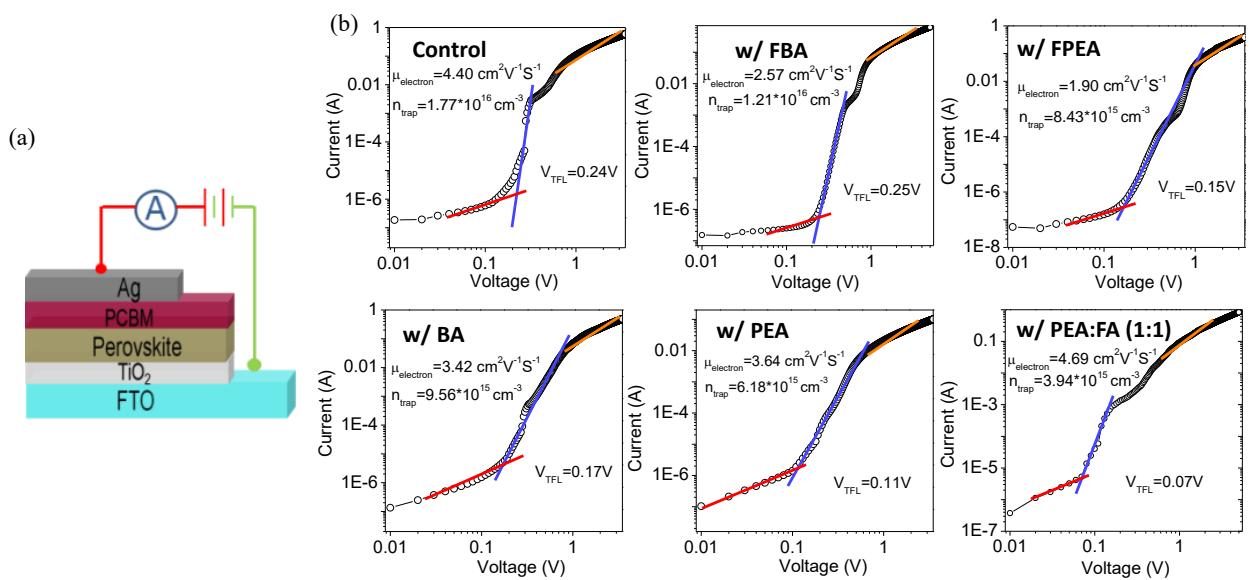
**Figure S5.** The dynamic evolution of the bleaching recovery for the control and 2D/3D films.



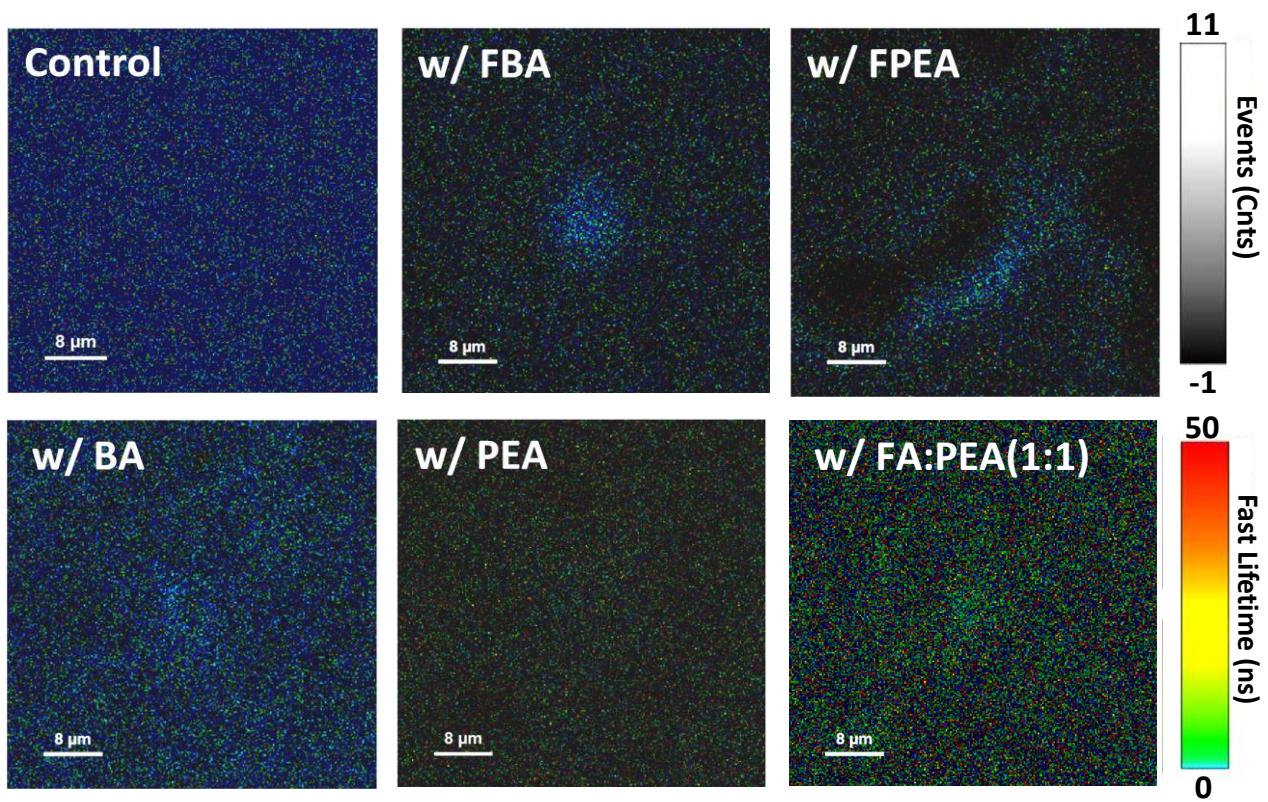
**Figure S6.** Transient absorption (TA) spectra at different delay times of the control and 2D/3D films under back-excitation.



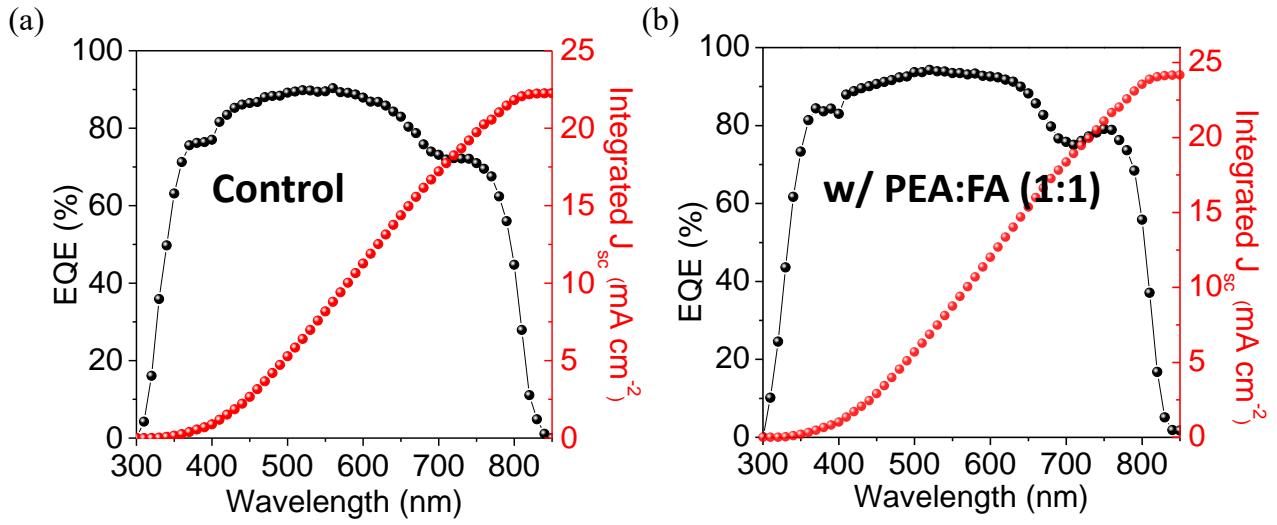
**Figure S7.** TA kinetics of control and 2D/3D films under back-excitation.



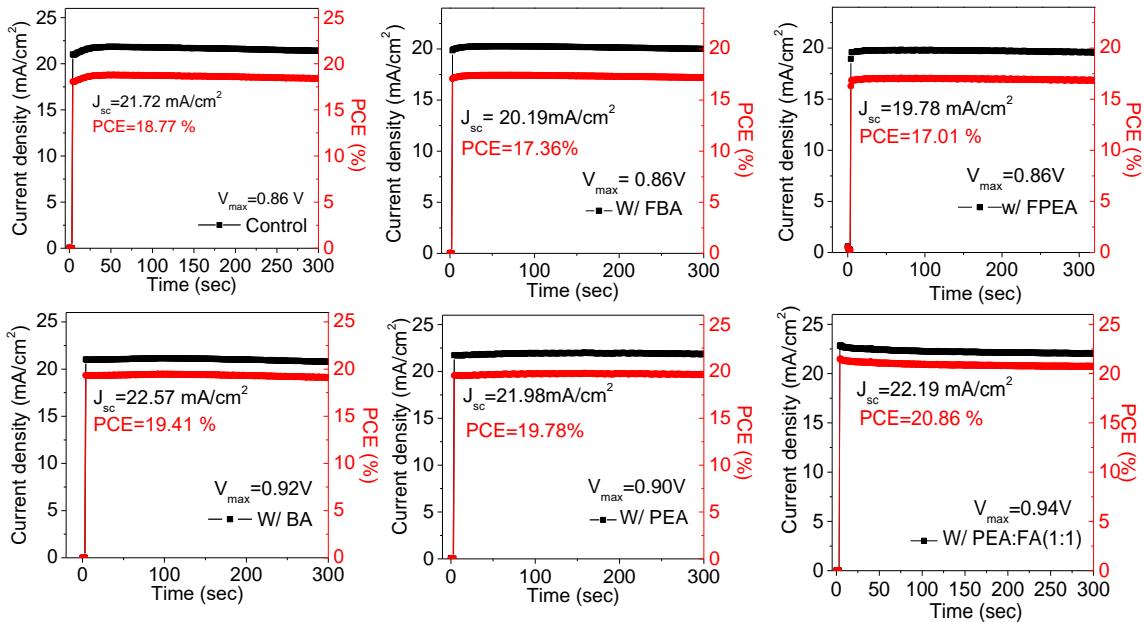
**Figure S8.** (a) The electron-only device structures. (b) Dark  $I$ - $V$  measurement of the electron-only devices for the control and 2D/3D films with different 2D capping layers displaying  $V_{\text{TFL}}$  kink point behavior.



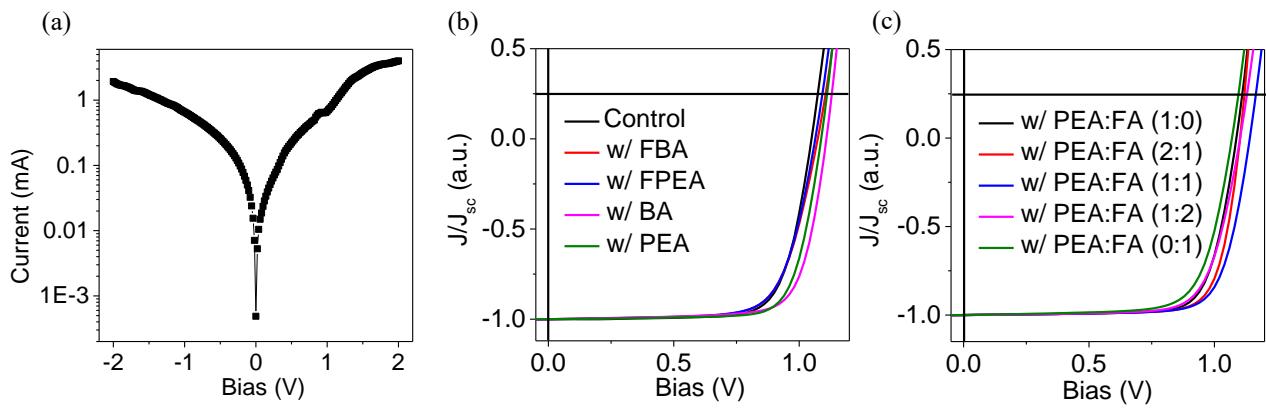
**Figure S9.** Overlapped intensity/lifetime PL mapping images of control and 2D/3D films (the excitation wavelength is 510 nm). The BA-, PEA- and PEA:FA(1:1)-based 2D/3D films exhibit the distinctly increased carrier lifetime accompanied with improved uniformity in contrast to the control film.



**Figure S10.** (a and b) External quantum efficiency (EQE) and the corresponding integrated short circuit density ( $J_{sc}$ ) for the champion devices obtained for the control and PEA:FA(1:1)-based 2D/3D films.



**Figure S11.** The stabilized power output of the champion devices for 2D/3D perovskite measured at a fixed maximum power point (MPP) voltage as a function of time.



**Figure S12.** (a) The dark J-V curve of the representative control device. The dark curve for the control device is significantly lower than the photocurrent of the same device, suggesting that the contributions from extrinsic resistances are slight to the slopes from  $J$ - $V$  curves at OC and SC. (b) and c) The normalized light  $J$ - $V$  curves of devices for the control and 2D/3D perovskites.

**Table S1.** Photovoltaic parameters of champion devices based on the control and 2D/3D films.

	V <sub>OC</sub> (V)	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF (%)	PCE (%)
Control	1.06	23.99	74.8	19.02
w/ FBA	1.07	22.63	72.0	17.51
w/ FPEA	1.06	22.13	72.8	17.14
w/ BA	1.11	23.12	76.0	19.50
w/ PEA	1.09	23.76	76.8	19.84
w/ PEA:FA(2:1)	1.10	23.50	78.3	20.28
w/ PEA:FA(1:1)	1.14	24.20	76.6	21.15
w/ PEA:FA(1:2)	1.10	23.69	74.5	19.46
w/ PEA:FA(0:1)	1.07	22.48	73.5	17.68

	V <sub>OC</sub> (V)	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF (%)	PCE (%)	PCE <sub>max</sub> (%)
Control	1.05±0.01	24.02±0.37	73.1±1.5	18.10±0.46	19.02
w/ FBA	1.05±0.02	22.57±0.31	71.5±2.1	16.95±0.40	17.51
w/ FPEA	1.05±0.01	22.19±0.23	71.8±1.0	16.64±0.65	17.14
w/ BA	1.09±0.02	23.13±0.12	74.7±0.9	18.42±0.42	19.50
w/ PEA	1.08±0.02	23.54±0.35	75.1±1.9	18.86±0.54	19.84
w/ PEA:FA(2:1)	1.07±0.02	23.46±0.32	75.0±1.2	18.71±0.51	20.28
w/ PEA:FA(1:1)	1.10±0.02	23.39±0.56	74.7±1.4	20.21±0.73	21.15
w/ PEA:FA(1:2)	1.06±0.02	23.01±0.42	71.4±1.7	17.47±0.89	19.46
w/ PEA:FA(0:1)	1.05±0.02	22.52±0.48	71.9±0.9	16.99±0.32	17.68

**Table S2.** Summaries of fitting parameters for time-resolved photoluminescence (TRPL) for the different films.

	Control	w/ FBA	w/ FPEA	w/ BA	w/ PEA	w/ PEA:FA(1:1)
A <sub>1</sub>	4446.7	2793.4	6020.6	3429.6	3551.4	7182.2
τ <sub>1</sub> (ns)	211.5	166.8	129.4	301.6	372.1	285.8
A <sub>2</sub>	4857.4	5155.2	4997.4	6496.5	5137.1	2163.3
τ <sub>2</sub> (ns)	50.1	23.3	27.5	57.3	58.9	83.0
τ <sub>ave</sub> (ns)	171.9	137.3	129.4	236.9	313.8	269.5

**Table S3.** The hysteresis parameters of devices based on the control and 2D/3D films.

	Scanning mode	V <sub>OC</sub> (V)	J <sub>SC</sub> (mA/cm <sup>2</sup> )	FF (%)	PCE (%)	Hysteresis index (%)
Control	Reverse	1.06	23.99	74.8	19.02	8.9
	Forward	1.02	23.56	71.8	17.32	
w/ FBA	Reverse	1.07	22.63	72.0	17.51	2.9
	Forward	1.07	22.30	71.3	17.00	
w/ FPEA	Reverse	1.06	22.13	72.8	17.14	5.0
	Forward	1.06	21.60	70.9	16.28	
w/ BA	Reverse	1.11	23.12	76.0	19.50	5.3
	Forward	1.09	22.69	74.9	18.46	
w/ PEA	Reverse	1.09	23.76	76.8	19.84	2.1
	Forward	1.08	23.70	76.0	19.43	
w/ PEA:FA(1:1)	Reverse	1.14	24.20	76.6	21.15	2.9
	Forward	1.13	24.12	75.7	20.54	